

4-8 GHz Low Noise Amplifier

Features:

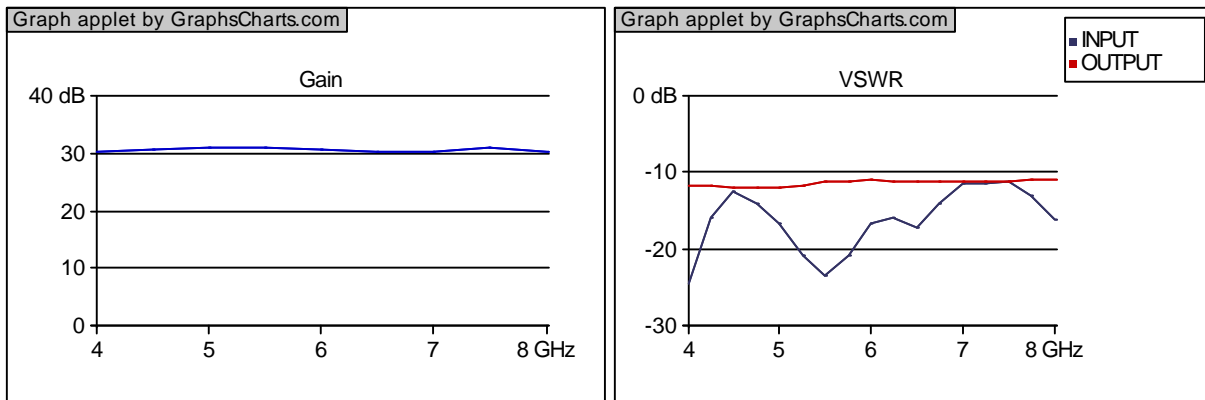
- Thin Film Hybrid MIC Process
- Field Replaceable RF Connectos
- Reverse Polarity Protection
- Wide Range of DC Supply Voltage

Electrical Performance

Parameter	Min.	Typ.	Max.	Unit	Note
Frequency	4		8	GHz	
Gain	29	30		dB	
Gain Flatness		0.5	1.0	dB(+/-)	
VSWR Input			2.0		
VSWR Output			2.0		
Power @ 1dB Gain Compression Point	15	16		dBm	
Noise Figure		1.7	2.2	dB	
DC Supply Voltage	10	15	17	V	
Supplied Current		90	110	mA	

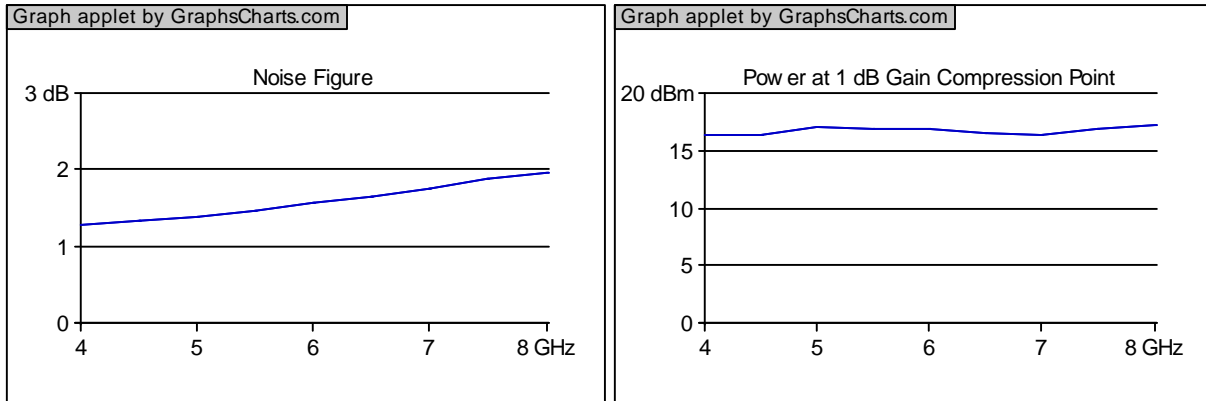
* RF Input Power: -15 dBm. DC Supply Voltage: +15 V.
 ** Measured at 25 degC.

Typical Test Data

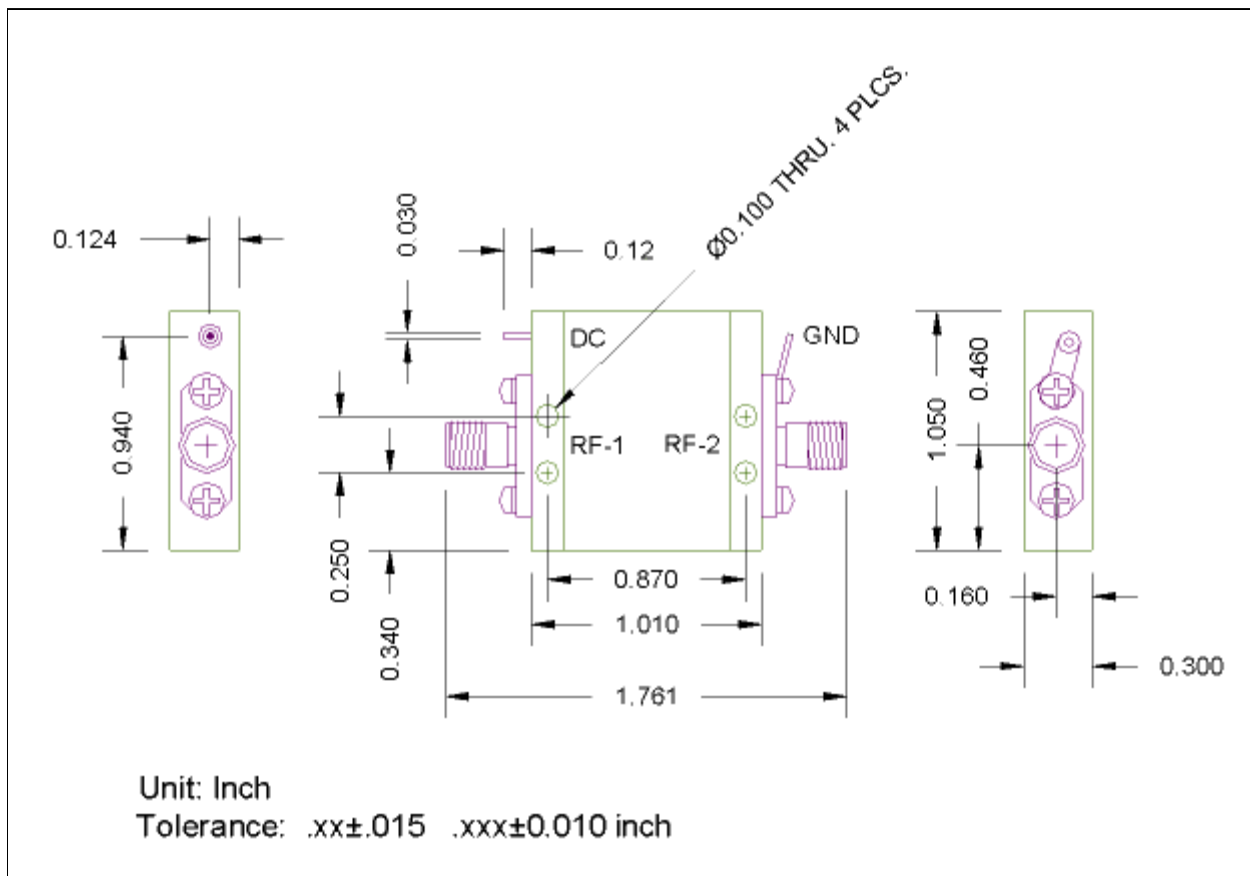


Updated: 12/2/2007

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Outline Drawing



Connector	Type	Pin #	Pin Name	In/Out	Description
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RF-1	SMA-F	1 IN	I	RF Input
RF-2	SMA-F	1 OUT	O	RF Output
DC	EMI Filter	1 +12 V	I	DC Power Supply (10-17V)
GND	GROUND LUG	1 GND	O	Ground

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